

# Assessing Al-ion conductors from sulphides and selenides

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Atom	Size	Polarisability	ICSD (Al + X)
O	Very small	none	10,077
S	Quite large	high	641
Se	large	high	153

## Motivation

- Electrochemical energy storage: most promising for **sustainable technologies**
- Aluminium (Al)**: high **abundance**, low price, high capacity (trivalent)
- So far no reliable Al<sup>3+</sup> **conductor/intercalation host** identified
- CryPhysConcept**: combine **crystallography**, **electrochemistry** and **resource aspects** to create new concepts for electrochemical energy storage
- Ion diffusion in crystals**: ion jump between two sites (via an intermediate)
- Shield** high charge of Al<sup>3+</sup>: find compounds with S/Se (**polarisability/size**)

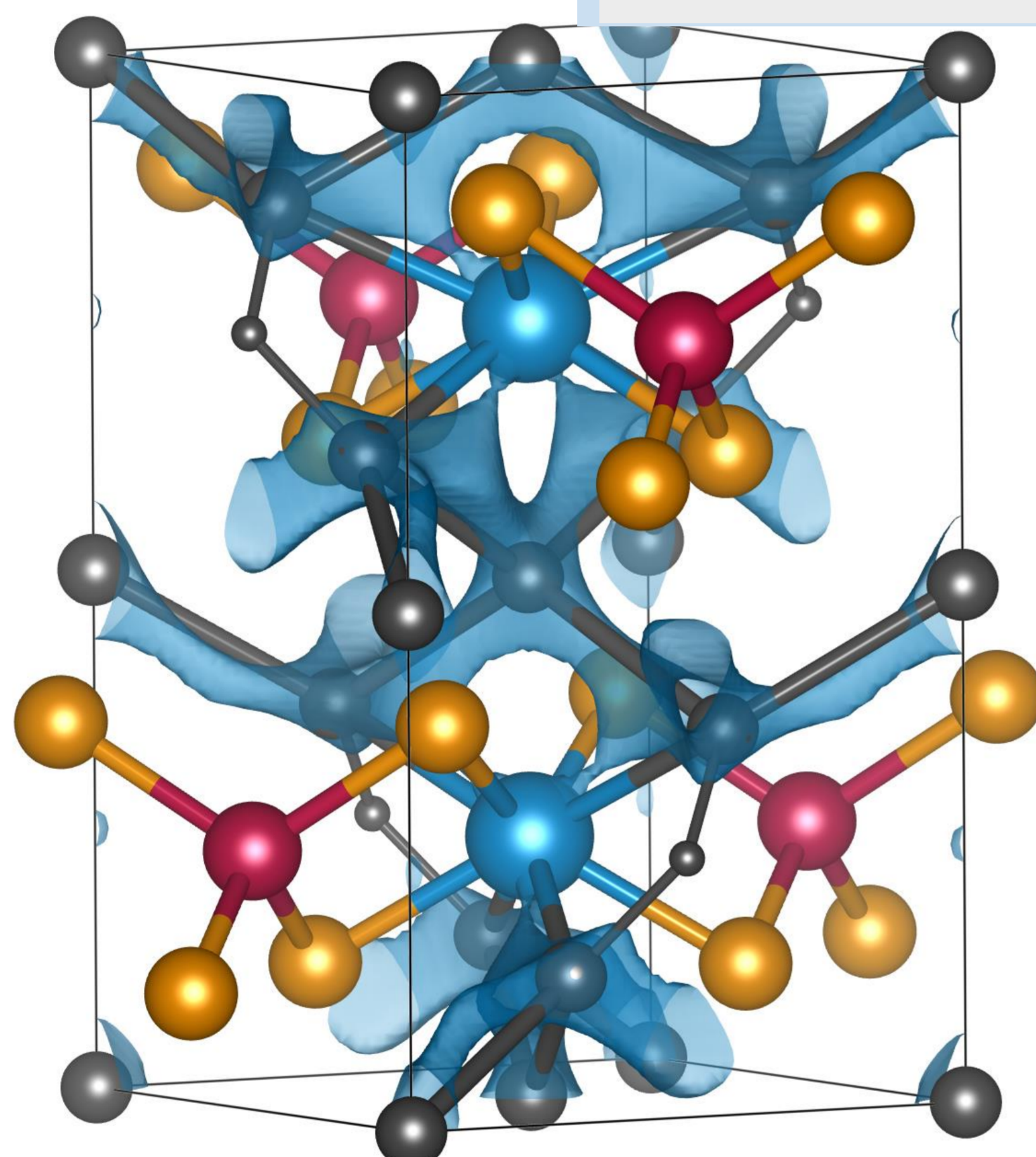
## Voronoi-Dirichlet Partitioning

- Data mine** reference values from ICSD: atomic soft sphere radii  $r_{SP}$  and crystal chemical data on **Al-S/Al-Se**
- Find most-promising entries from all **Al and S/Se containing compounds**
- Compare all **structural voids** with reference values [1] (c.f. Meutzner, *Cryst. Res. Technol.* **52**, 1600223 (2017))
- Calculation time: **fraction of a second** per compound

→ **37 + 5 promising structures**

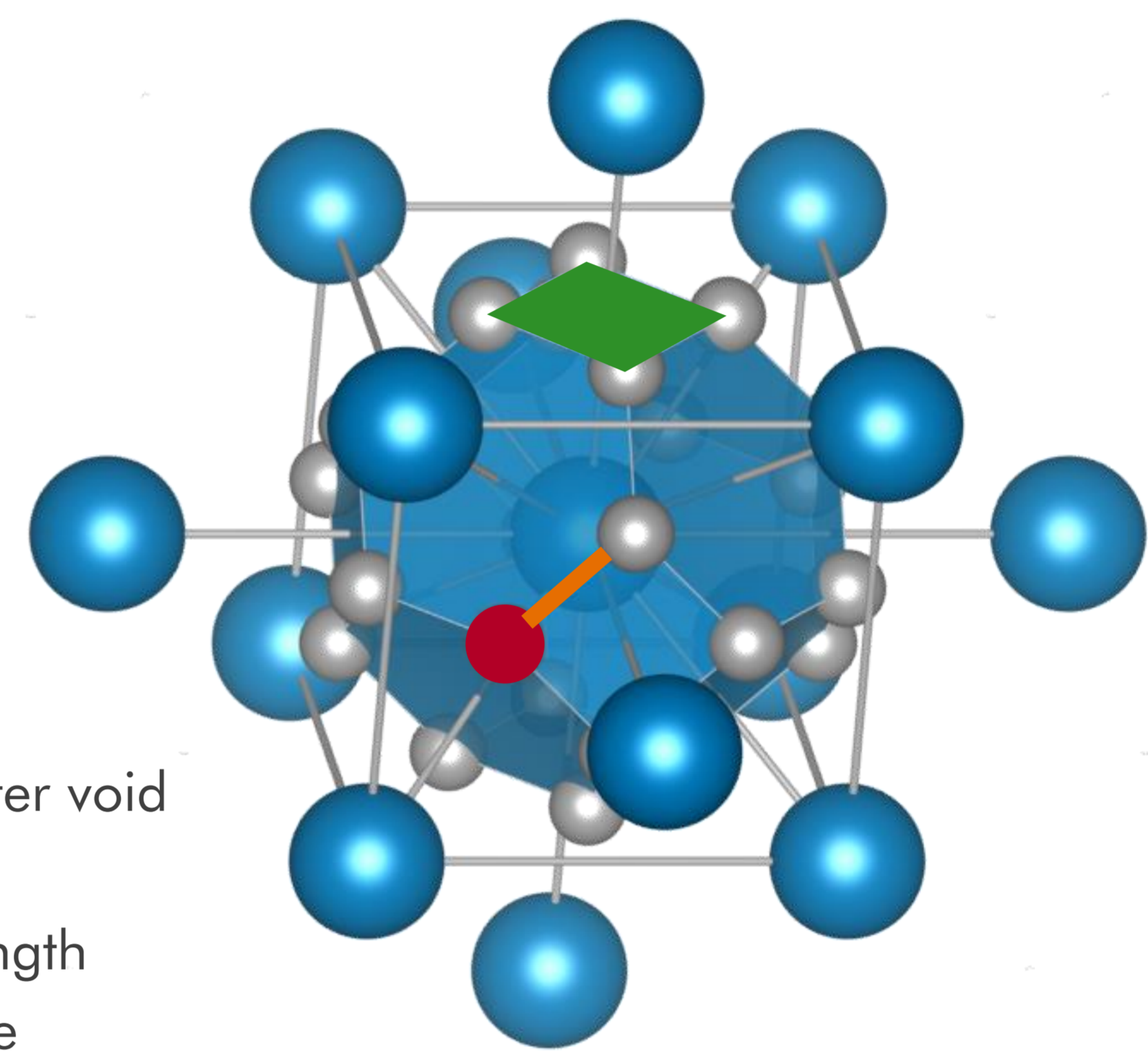
### Comments

Cell and Type only determined  
Atom positions estimated by editor, not refined



### Ionic Conductivity

- Vertices** — voids possible ions to enter void
- Edges** — channels
- Faces** — bond strength
- Volume** — ionic size



## Bond-Valence Energy-Landscape

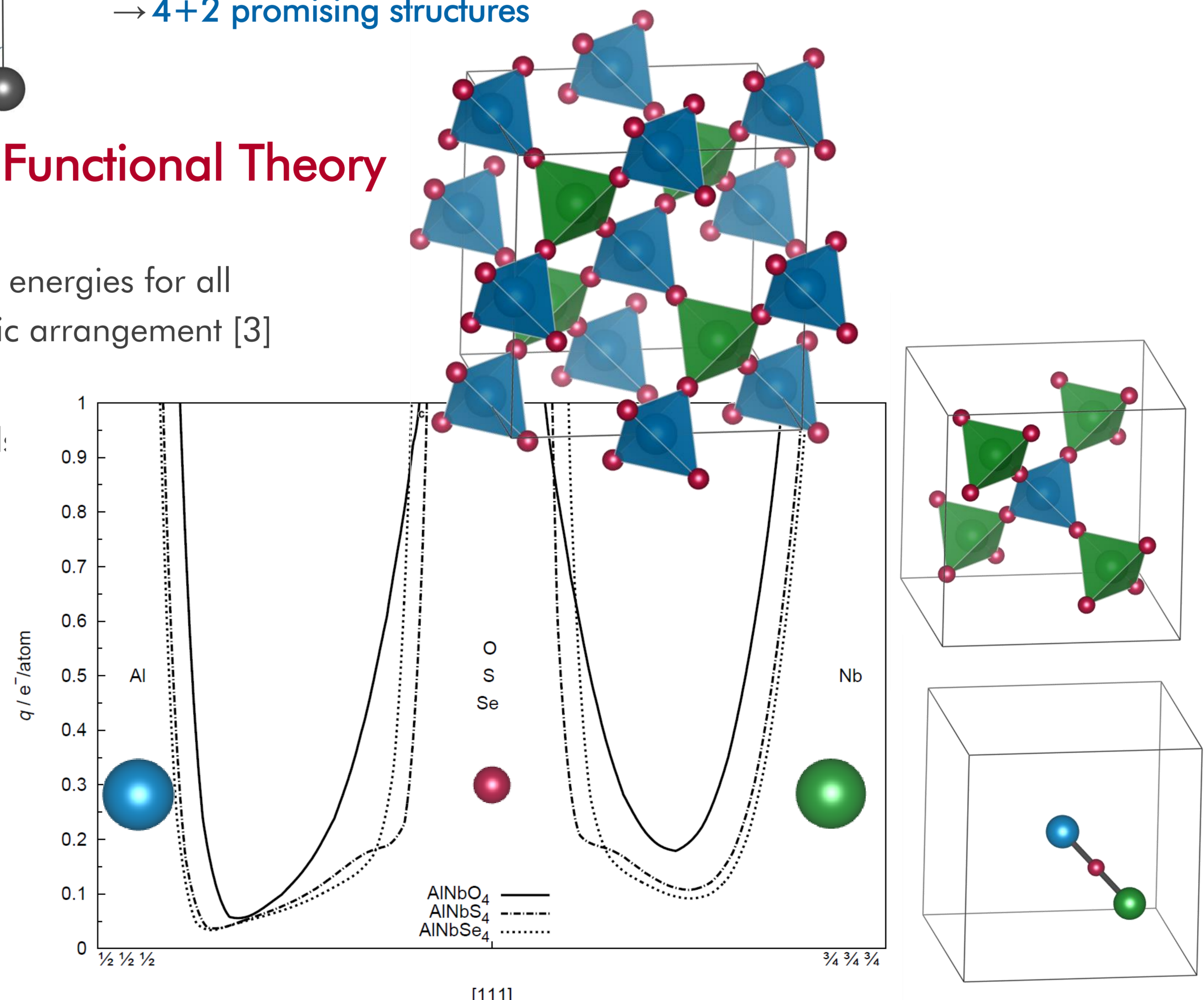
- Translate **bond-valence sum mismatch** into energy [2]
  - Calculate for the **whole crystal volume** (resolution of 0.1 Å)
  - Find lowest energy barrier → **activation energy** for diffusion
  - Calculate for Al<sup>3+</sup>, S<sup>2-</sup>/Se<sup>2-</sup> and all other remaining elements
  - Calculation time: **minutes to hours** per compound
- **4+2 promising structures**

## Density Functional Theory

- Calculate **electronic configuration ab initio**
  - Nudged Elastic Bands (NEB)** algorithm calculates energies for all **intermediate steps** between initial and final atomic arrangement [3]
  - Each step is **fully electronically relaxed**
  - Only done for a very small amount of compound:
  - Calculation: **hours to days** per compound
- Work in progress

## Summary & Outlook

- Combination of **advantages** into new algorithm
  - Applicable for **any sort of ion**
  - Efficient in **time and conclusion**
  - Synergies bring **development** for each method
  - Experimental **proof-of-principle**
- Full results to be submitted in 2016



[1] Blatov et al.: *Acta Crystallogr. B* **62**, 1010–1018 (2006).

[2] Adams et al.: *Physica Status Solidi A* **208**, 1746 (2011).

[3] Kresse et al.: *Phys. Rev. B* **54**, 11169 (1996).